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SCR

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	300	-	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	А - К
2	Α	anode		Ġ sym037
3	G	gate		Symoor.
mb	n.c.	mounting base; isolated	TO-220F (SOT186A)	

6. Ordering information

Table 3. Ordering information

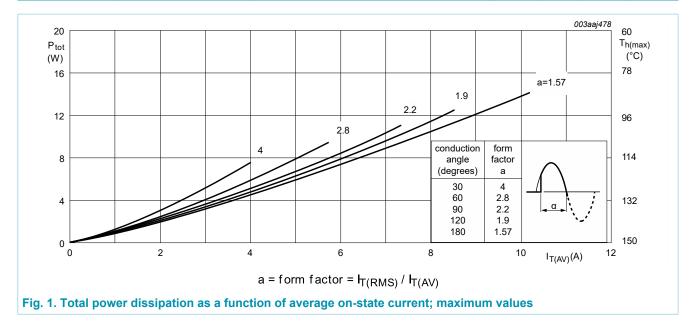
Type number	Package				
	Name	Description	Version		
TYN16X-600RT	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
V_{RRM}	repetitive peak reverse voltage		-	600	V
I _{T(AV)}	average on-state current	half sine wave; T _h ≤ 86 °C; <u>Fig. 1</u>	-	10.2	Α
I _{T(RMS)}	RMS on-state current	half sine wave; T _h ≤ 86 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	16	Α
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 10 \text{ms}$; Fig. 4; Fig. 5	-	210	Α
		half sine wave; T _{j(init)} = 25 °C; t _p = 8.3 ms	-	231	Α
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	220.5	A²s
dl _T /dt	rate of rise of on-state current	I _G = 50 mA	-	50	A/µs
I _{GM}	peak gate current		-	5	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C



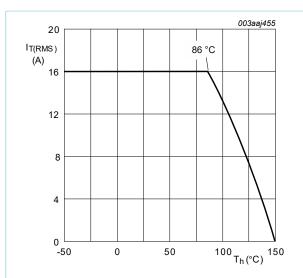
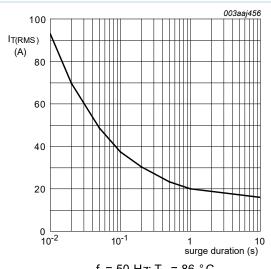


Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values



 $f = 50 \text{ Hz}; T_h = 86 ° C$

Fig. 3. RMS on-state current as a function of surge duration; maximum values

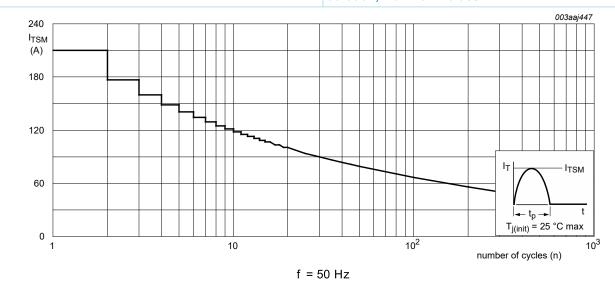
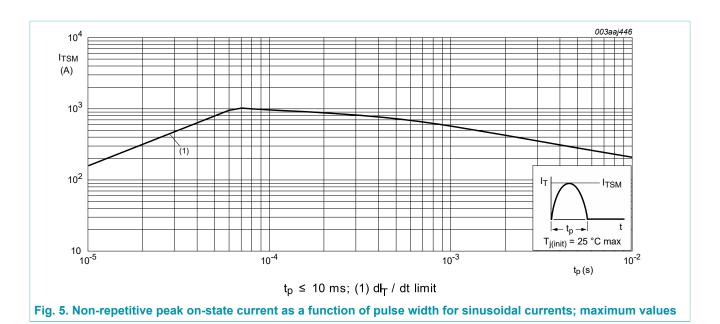


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

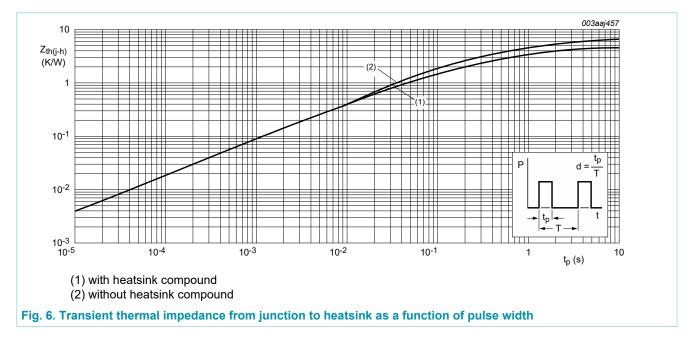


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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance	with heatsink compound; Fig. 6	-	-	4.5	K/W
	from junction to heatsink	without heatsink compound; Fig. 6	-	-	6.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



9. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from anode to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	_	pF

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 7</u>	-	4.5	25	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 8$	-	21	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	16	40	mA
V_T	on-state voltage	I _T = 32 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1.3	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 \text{ °C};$ Fig. 11	0.2	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 150 °C	-	0.2	1	mA
I _R	reverse current	V _R = 600 V; T _j = 150 °C	-	0.2	1	mA
Dynamic ch	naracteristics		·			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	300	-	-	V/µs

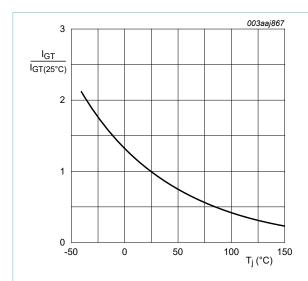


Fig. 7. Normalized gate trigger current as a function of junction temperature

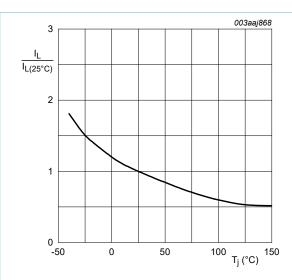


Fig. 8. Normalized latching current as a function of junction temperature

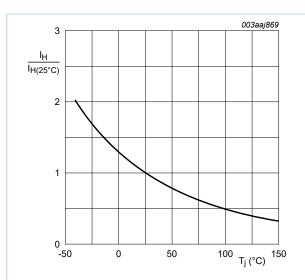
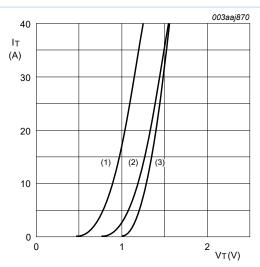


Fig. 9. Normalized holding current as a function of junction temperature



 V_0 = 1.0336 V; R_s = 0.0141 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_j = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

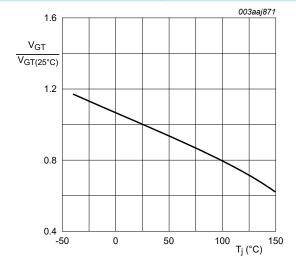


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

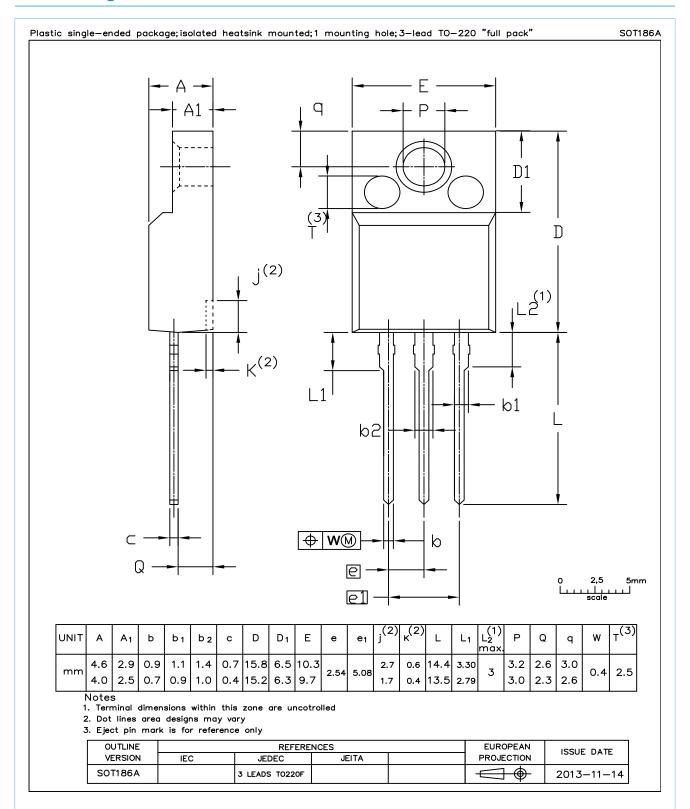


Fig. 12. Package outline TO-220F (SOT186A)

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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For more information, please visit: http://www.ween-semi.com For sales office addresses, please send an email to: salesaddresses@ween-semi.com Date of release: 3 September 2018

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